

FREQUENCY MODULATION OF RECOMBINATION
RADIATION EMITTED BY AN InAs/GaAs
HETEROSTRUCTURE WITH InAs QUANTUM
DOTS UNDER THE INFLUENCE
OF AN ACOUSTIC WAVE

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S u m m a r y

We have developed a theoretical model that describes the process of frequency modulation of radiation emitted at the recombination transition between the ground states of an electron and a hole in the InAs/GaAs heterostructure with InAs/GaAs quantum dots, the modulation being induced by an acoustic wave. The character of the dependence of the frequency modulation amplitude on the acoustic wave frequency is determined.